

TSM7N90 Taiwan Semiconductor

ALOGEN

# **N-Channel Power MOSFET**

 $900V,\,7A,\,1.9\Omega$ 

#### FEATURES

- Low RDS(on) 1.9Ω (Max.)
- Low gate charge typical @49nC (Typ.)
- Improve dV/dt capability
- Pb-free plating
- Compliant to RoHS Directive 2011/65/EU and in accordance to WEE 2002/96/EC

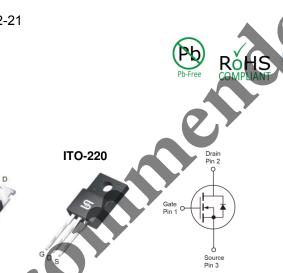
**TO-220** 

Halogen-free according to IEC 61249-2-21
definition

#### APPLICATION

- Power Supply
- Lighting

KEY PERFORMANCE PARAMETERSPARAMETERVALUEUNIT $V_{DS}$ 900V $R_{DS(on)}$  (max)1.9 $\Omega$  $Q_g$ 49nC



ABSOLUTE MAXIMUM RATINGS (T <sub>A</sub> = 25°C unless otherwise noted)							
PARAMETER		SYMBOL	TO-220	ITO-220	UNIT		
Drain-Source Voltage		V <sub>DS</sub>	900		V		
Gate-Source Voltage		$V_{GS}$	±30		V		
Continuous Drain Current (Note 1)	T <sub>C</sub> = 25°C	l <sub>D</sub>	7		А		
	T <sub>C</sub> = 100°C		4.31		А		
Pulsed Drain Current (Note 2)		I <sub>DM</sub>	28		А		
Total Power Dissipation @ $T_c = 25^{\circ}C$		P <sub>DTOT</sub>	250	40.3	W		
Single Pulsed Avalanche Energy (Note 3)		E <sub>AS</sub>	106		mJ		
Single Pulsed Avalanche Current (Note 3)		I <sub>AS</sub>	7		А		
Operating Junction and Storage Temperature Range		$T_J, T_STG$	- 55 to +150		°C		

THERMAL PERFORMANCE				
PARAMETER	SYMBOL	TO-220	ITO-220	UNIT
Junction to Case Thermal Resistance	R <sub>ejc</sub>	0.5	3.1	°C/W
Junction to Ambient Thermal Resistance	$R_{\Theta JA}$	62.5		°C/W

**Notes:**  $R_{\Theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistances. The case thermal reference is defined at the solder mounting surface of the drain pins.  $R_{\Theta JA}$  is guaranteed by design while  $R_{\Theta CA}$  is determined by the user's board design.  $R_{\Theta JA}$  shown below for single device operation on FR-4 PCB with minimum recommended footprint in still air.



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PARAMETER	CONDITIONS	SYMBOL	MIN	TYP	MAX	UNIT
Static (Note 4)	•	L			1	
Drain-Source Breakdown Voltage	$V_{GS} = 0V, I_D = 250 \mu A$	BV <sub>DSS</sub>	900			V
Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = 250 \mu A$	V <sub>GS(TH)</sub>	2		4	V
Gate Body Leakage	$V_{GS} = \pm 30V, V_{DS} = 0V$	I <sub>GSS</sub>			±100	nA
Zero Gate Voltage Drain Current	V <sub>DS</sub> = 900V, V <sub>GS</sub> = 0V	I <sub>DSS</sub>			10	μA
Drain-Source On-State Resistance	$V_{GS}$ = 10V, $I_{D}$ = 3.5A	R <sub>DS(on)</sub>		1.52	1.9	Ω
Dynamic (Note 5)						
Total Gate Charge		Qg		49		nC
Gate-Source Charge	$V_{DS} = 720V, I_D = 7A,$	Q <sub>gs</sub>	/	7		
Gate-Drain Charge	V <sub>GS</sub> = 10V	Q <sub>gd</sub>		20		
Input Capacitance		C <sub>iss</sub>		1969		pF
Output Capacitance	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V, f = 1.0MHz	C <sub>oss</sub>		133		
Reverse Transfer Capacitance		Crss		11		
Switching (Note 6)						
Turn-On Delay Time	$V_{DD} = 380V,$ $R_{GEN} = 25\Omega,$ $I_D = 10A, V_{GS} = 10V,$	t <sub>d(on)</sub>		39		ns
Turn-On Rise Time		t <sub>r</sub>		38		
Turn-Off Delay Time		t <sub>d(off)</sub>		155		
Turn-Off Fall Time		t <sub>f</sub>		45		
Source-Drain Diode (Note 4)						
Forward On Voltage	I <sub>S</sub> = 10A, V <sub>GS</sub> = 0V	V <sub>SD</sub>			1.4	V
Reverse Recovery Time	I <sub>S</sub> = 7A,	t <sub>rr</sub>		464		ns
Reverse Recovery Charge	dl <sub>F</sub> /dt = 100A/µs	Q <sub>rr</sub>		4.7		μC

1. Current limited by package.

2.

Pulse width limited by the maximum junction temperature. L = 4.1mH,  $I_{AS}$ = 7A,  $V_{DD}$  = 50V,  $R_G$  = 25 $\Omega$ , Starting T<sub>J</sub> = 25°C 100% Eas Test Condition: L = 1mH,  $I_{AS}$  = 3.5A,  $V_{DD}$  = 50V,  $R_G$  = 25 $\Omega$ , Starting T<sub>J</sub> = 25°C 3.

4. Pulse test:  $PW \le 300\mu s$ , duty cycle  $\le 2\%$ .

For DESIGN AID ONLY, not subject to production testing. 5.

Switching time is essentially independent of operating temperature. 6.

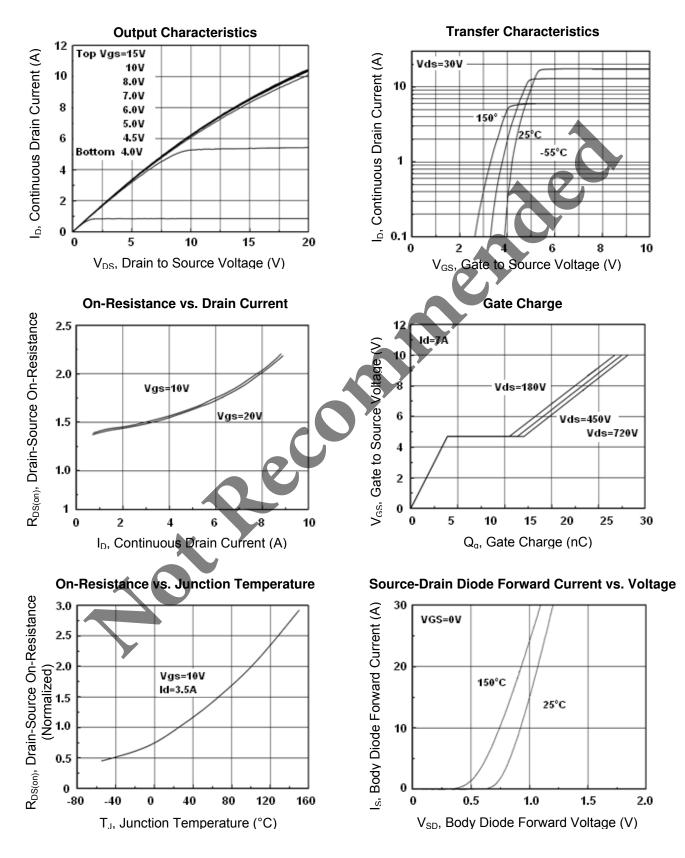


#### ORDERING INFORMATION



### CHARACTERISTICS CURVES

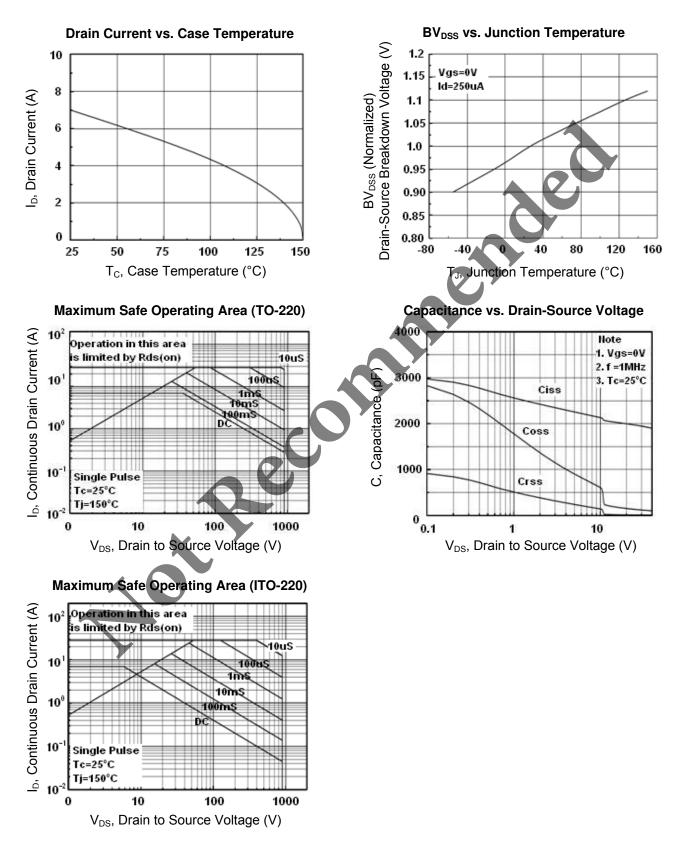
(T<sub>C</sub> = 25°C unless otherwise noted)





### CHARACTERISTICS CURVES

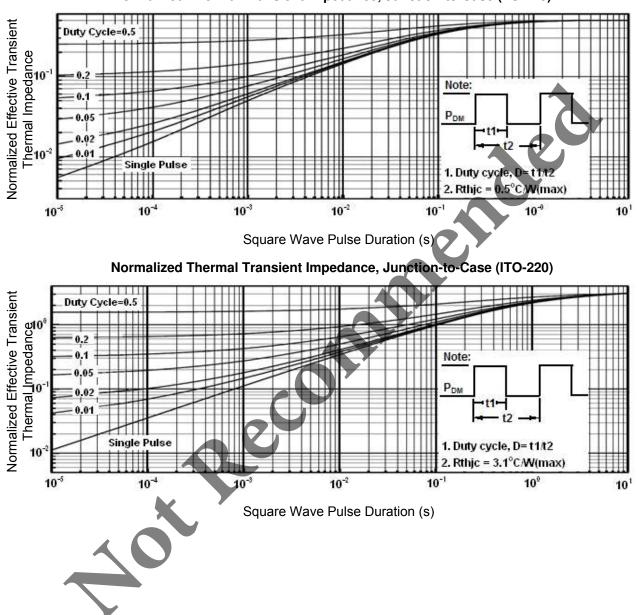
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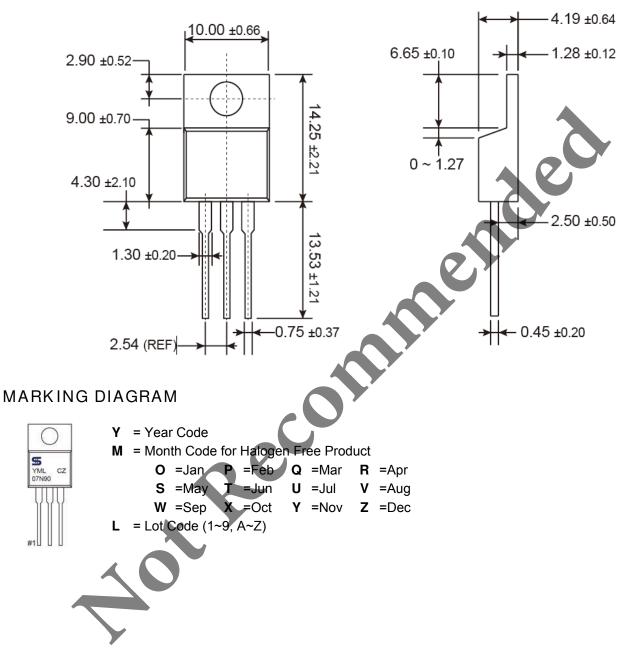
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Normalized Thermal Transient Impedance, Junction-to-Case (TO-220)



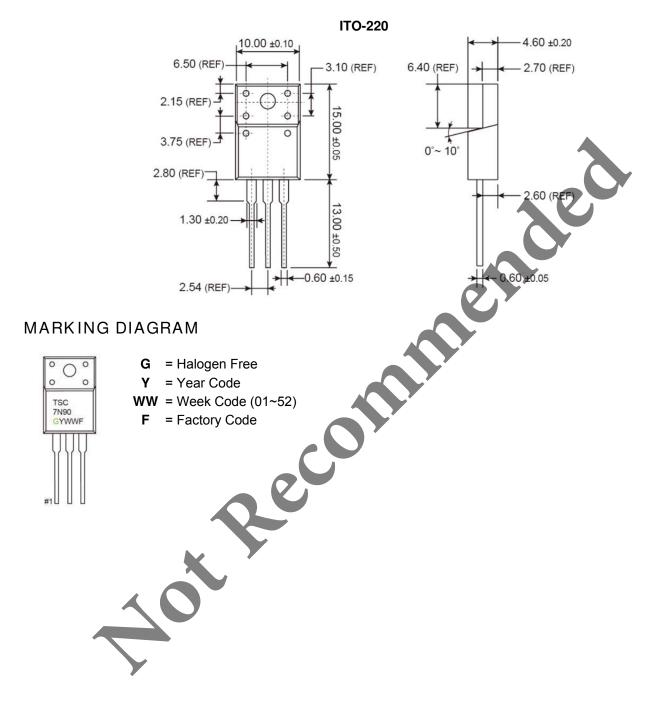
#### PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)



TO-220



## PACKAGE OUTLINE DIMENSIONS (Unit: Millimeters)







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